

Application/Control No.

Applicant(s)/Patent Under

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-6,404,222	06-2002	Fan et al.	324/765
	В	US-			
	С	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	н	US-			
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	К	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)				
	U	Chen et al (An On-Chip, Attofarad Interconnect Charge-Based Capacitance Measurement (CBCM) Technique, Chen, J.C.; McGaughy, B.W.; Sylvester, D.; Chenming Hu, Electron Devices Meeting, International, 8-11 Dec. 1996, Pages: 69 - 72)				
	v	McGaughy et al (A Simple Method for On-Chip, Sub-Femto Farad Interconnect Capacitance Measurement, McGaughy, B.W.; Chen, J.C.; Sylvester, D.; Chenming Hu; Electron Device Letters, IEEE ,Volume: 18, Issue: 1 , Jan. 1997, Pages: 21 – 23)				
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

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